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(54) **METHOD OF MANUFACTURING SEMICONDUCTOR DEVICES AND CORRESPONDING SEMICONDUCTOR DEVICE**

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(57) **ABSTRACT**

A method comprises molding laser direct structuring material onto at least one semiconductor die, forming resist material on the laser direct structuring material, producing mutually aligned patterns of electrically-conductive formations in the laser direct structuring material and etched-out portions of the resist material having lateral walls sidewise of said electrically-conductive formations via laser beam energy, and forming electrically-conductive material at said etched-out portions of the resist material, the electrically-conductive material having lateral confinement surfaces at said lateral walls of said etched-out portions of the resist material.

